



YJQ018G10AHQ

N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	100V
I_D	40A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	18m
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	22.5m
100% EAS Tested	
100% V_{DS} Tested	

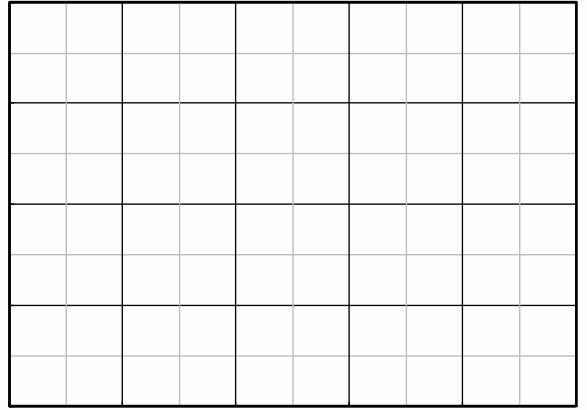
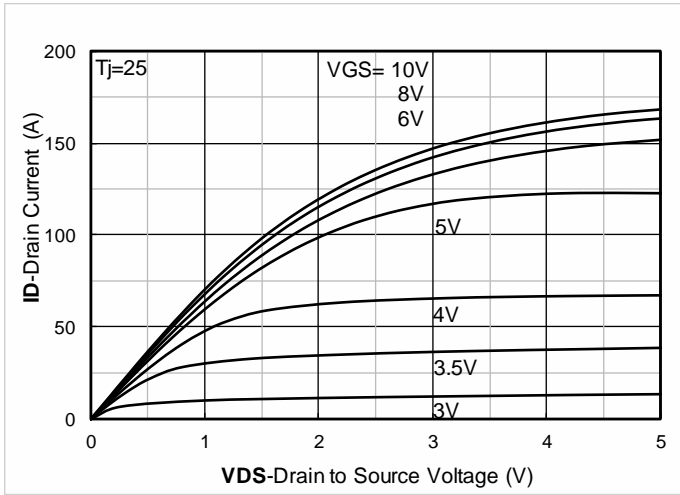
General Description

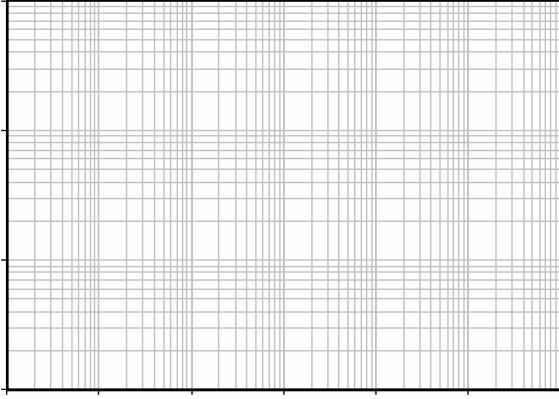
Excellent package for heat dissipation
High density cell design for low $R_{DS(ON)}$
Moisture Sensitivity Level 1
Epoxy Meets UL 94 V-0 Flammability Rating

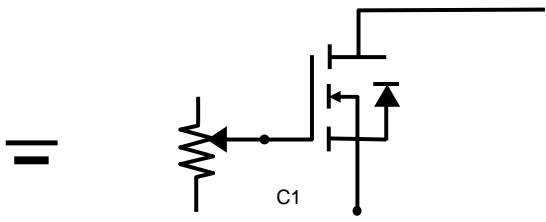


YJQ018G10AHQ

Typical Electrical and Thermal Characteristics Diagrams







t))

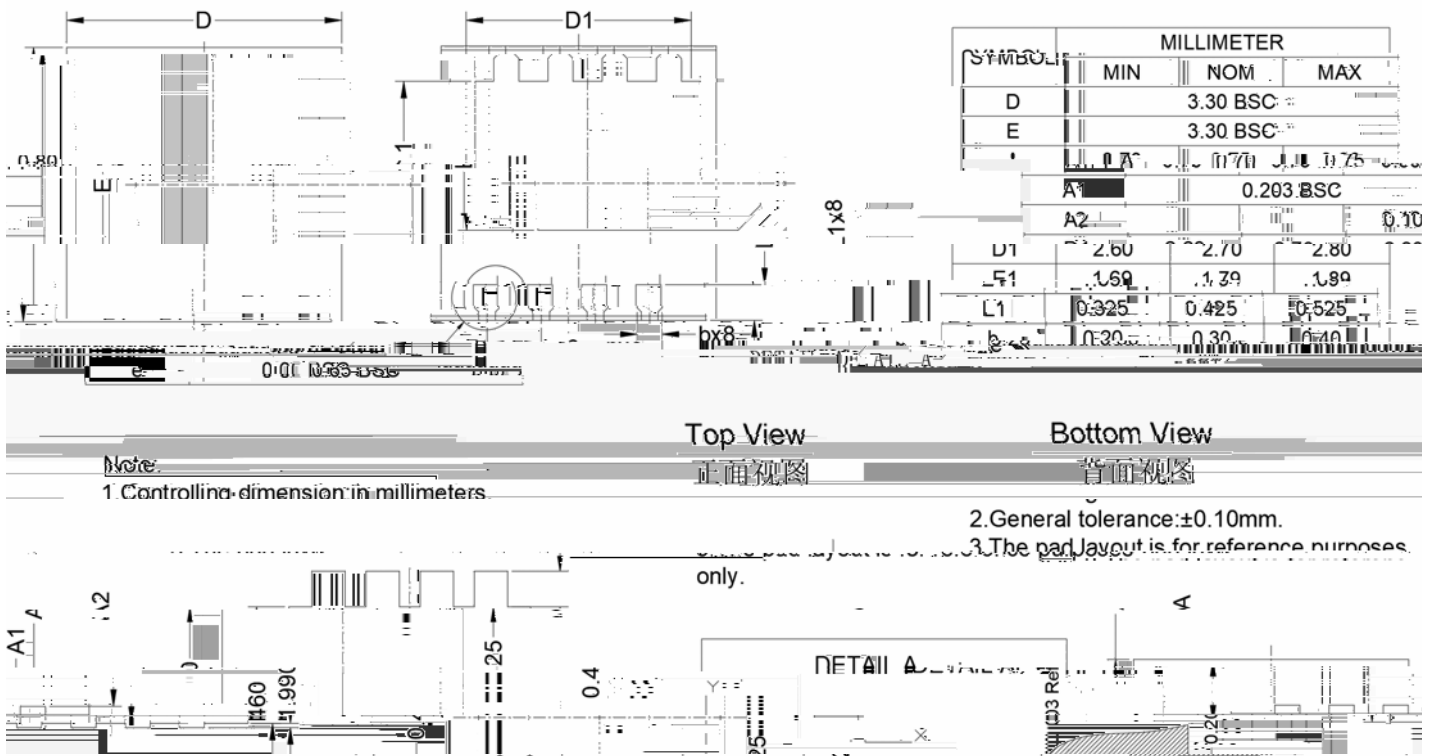
)yu





YJQ018G10AHQ

DFN3333-8L-WF Package information





YJQ018G10AHQ

Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with automotive electronics, are not designed for use in medical, life-saving, lifesustaining, or military, Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website <http://www.21yangjie.com> , or consult your nearest Yangjie's sales office for further assistance.